

# Razali Ismail

## List of Publications by Year in descending order

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times ranked

1658  
citing authors

#	ARTICLE	IF	CITATIONS
1	Analysis and Modeling of White Graphene Physical Properties for Sensor Applications. Proceedings of the National Academy of Sciences India Section A - Physical Sciences, 2020, 90, 475-479.	1.2	4
2	Reliability Analysis Of Gate-All-Around Floating Gate (GAA-FG) With Variable Oxide Thickness For Flash Memory Cell. , 2020, , .		0
3	Centroid and Inversion Charge Model for Long Channel Strained-Silicon GAA MOSFET with Quantum Effect. , 2020, , .		0
4	Estimation of pull-in phenomena in carbon nanotubes based micro/nanobeam cantilevers. AIP Conference Proceedings, 2020, , .	0.4	0
5	Effect of solution pH and adsorbent concentration on the sensing parameters of TGNâ€based electrochemical sensor. IET Nanobiotechnology, 2019, 13, 584-592.	3.8	4
6	Optimization of a Hydrothermal Growth Process for Low Resistance 1D Fluorine-Doped Zinc Oxide Nanostructures. Journal of Nanomaterials, 2019, 2019, 1-10.	2.7	15
7	Effect of post annealing treatment on electrical and structural properties of zinc oxide nanostructures. Materials Today: Proceedings, 2019, 7, 710-714.	1.8	3
8	Quantum Capacitance Model for Graphene FET-Based Gas Sensor. IEEE Sensors Journal, 2019, 19, 3726-3732.	4.7	17
9	Effect of low-k oxide thickness variation on gate-all-around floating gate with optimized SiO <sub>2</sub> /La <sub>2</sub> O <sub>3</sub> tunnel barrier. Materials Research Express, 2019, 6, 1150c6.	1.6	0
10	A carrier velocity model for electrical detection of gas molecules. Beilstein Journal of Nanotechnology, 2019, 10, 644-653.	2.8	1
11	The effects of a Stoneâ€Wales defect on the performance of a graphene-nanoribbon-based Schottky diode. Journal of Computational Electronics, 2019, 18, 802-812.	2.5	9
12	Investigating the electrical characteristics of a single electron transistor utilizing graphene nanoribbon as the island. Journal of Materials Science: Materials in Electronics, 2019, 30, 8007-8013.	2.2	10
13	Impact of Chiral Indices on the Performance of Single Electron Transistor Utilizing Carbon Nanotube Island. ECS Journal of Solid State Science and Technology, 2019, 8, M26-M29.	1.8	3
14	Explicit continuous models of drain current, terminal charges and intrinsic capacitance for a long-channel junctionless nanowire transistor. Physica Scripta, 2019, 94, 105813.	2.5	10
15	Optimisation of Short Channel Strained Silicon Surrounding Gate MOSFET using Variable Oxide Thickness (VARIOT) for Low Power Application. , 2019, , .		0
16	Stacking SiO <sub>2</sub> / High-\$\$\$ Dielectric Material in 30nm Junction-less Nanowire Transistor Optimized Using Taguchi Method for Lower Leakage Current. , 2019, , .		1
17	The impact of vacancy defects on the performance of a single-electron transistor with a carbon nanotube island. Journal of Computational Electronics, 2019, 18, 428-435.	2.5	10
18	Scaling Challenges of Floating Gate Non-Volatile Memory and Graphene as the Future Flash Memory Device: A Review. Journal of Nanoelectronics and Optoelectronics, 2019, 14, 1195-1214.	0.5	7

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19	The Geometry Variation Effect on Carbon Atom Wire for Nano-Electronic Applications. Journal of Nanoelectronics and Optoelectronics, 2019, 14, 1120-1125.	0.5	5
20	Analytical Prediction of Conductance Model on Graphene Nanoscrolls. Advanced Science, Engineering and Medicine, 2019, 11, 525-531.	0.3	0
21	Performance analysis of one dimensional BC <sub>2</sub> N for nanoelectronics applications. Physica E: Low-Dimensional Systems and Nanostructures, 2018, 102, 33-38.	2.7	8
22	An analytical approach to model capacitance and resistance of capped carbon nanotube single electron transistor. AEU - International Journal of Electronics and Communications, 2018, 90, 97-102.	2.9	28
23	Photocatalytic degradation of 1,2-dichlorobenzene using immobilized TiO <sub>2</sub> /SnO <sub>2</sub> /WO <sub>3</sub> photocatalyst under visible light: Application of response surface methodology. Arabian Journal of Chemistry, 2018, 11, 34-47.	4.9	29
24	Analytical modelling and simulation of gas adsorption effects on graphene nanoribbon electrical properties. Molecular Simulation, 2018, 44, 551-557.	2.0	8
25	Graphene as Charge Storage Layer in Floating Gate Flash Memory with High-k Tunnel Barrier Engineering. , 2018, , .		0
26	Impact of Hydrogen Adsorption on the Performance of a Single Electron Transistor Utilizing Fullerene Quantum Dots. ECS Journal of Solid State Science and Technology, 2018, 7, M191-M194.	1.8	4
27	Single Electron Transistor Scheme Based on Multiple Quantum Dot Islands: Carbon Nanotube and Fullerene. ECS Journal of Solid State Science and Technology, 2018, 7, M145-M152.	1.8	17
28	Preparation, characterization, and lead removal appraisal of zinc aluminate prepared at different calcination temperatures. Journal of the Chinese Chemical Society, 2018, 65, 1199-1209.	1.4	5
29	Analysis and Modeling of Fullerene Single Electron Transistor Based on Quantum Dot Arrays at Room Temperature. Journal of Electronic Materials, 2018, 47, 4799-4806.	2.2	13
30	Analysis and modeling of quantum capacitance on graphene single electron transistor. International Journal of Modern Physics B, 2018, 32, 1850235.	2.0	9
31	Carbon Nano-particle Synthesized by Pulsed Arc Discharge Method as a Light Emitting Device. Journal of Electronic Materials, 2018, 47, 4003-4009.	2.2	7
32	Analysis of Co-Tunneling Current in Fullerene Single-Electron Transistor. Brazilian Journal of Physics, 2018, 48, 406-410.	1.4	5
33	Experimental and theoretical investigation of sensing parameters in carbon nanotube-based DNA sensor. IET Nanobiotechnology, 2018, 12, 1125-1129.	3.8	5
34	Toxic metals in Perna viridis mussel and surface seawater in Pasir Gudang coastal area, Malaysia, and its health implications. Environmental Science and Pollution Research, 2018, 25, 30224-30235.	5.3	17
35	Analysis and Simulation of Coulomb Blockade and Coulomb Diamonds in Fullerene Single Electron Transistors. Journal of Nanoelectronics and Optoelectronics, 2018, 13, 138-143.	0.5	11
36	Carrier Transport, Current-Voltage Characteristics of BGN. , 2018, , 163-185.		0

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37	Analytical Modeling of Current-Voltage Characteristics of Phosphorene Based Field Effect Transistor. Journal of Nanoelectronics and Optoelectronics, 2018, 13, 1478-1481.	0.5	0
38	Electrical Properties of MWCNT/HDPE Composite-Based MSM Structure Under Neutron Irradiation. Journal of Electronic Materials, 2017, 46, 2548-2555.	2.2	8
39	Current Analysis and Modeling of Fullerene Single-Electron Transistor at Room Temperature. Journal of Electronic Materials, 2017, 46, 4294-4298.	2.2	16
40	Gas adsorption effect on the graphene nanoribbon band structure and quantum capacitance. Adsorption, 2017, 23, 767-777.	3.0	19
41	Graphene Based Biosensor Model for <i>Escherichia Coli</i> Bacteria Detection. Journal of Nanoscience and Nanotechnology, 2017, 17, 601-605.	0.9	20
42	Graphene/Graphene Oxide-Based Ultrasensitive Surface Plasmon Resonance Biosensor. Plasmonics, 2017, 12, 1991-1997.	3.4	29
43	Carrier relaxation time modelling of monolayer black phosphorene. Micro and Nano Letters, 2017, 12, 758-762.	1.3	3
44	Band gap engineering of BC <sub>2</sub> N for nanoelectronic applications. Superlattices and Microstructures, 2017, 112, 328-338.	3.1	16
45	Method for polychlorinated biphenyls removal from mussels and its photocatalytic dechlorination. Applied Catalysis B: Environmental, 2017, 218, 327-337.	20.2	11
46	The Effect of Molecular Adsorption on Electro-Optical Properties of Graphene-Based Sensors. Plasmonics, 2017, 12, 1193-1198.	3.4	5
47	Analytical study of the electronic properties of boron nitride nanosheet. , 2017, , .		2
48	Modeling Trilayer Graphene-Based DET Characteristics for a Nanoscale Sensor. Advances in Computer and Electrical Engineering Book Series, 2017, , 19-38.	0.3	2
49	Graphene and CNT Field Effect Transistors Based Biosensor Models. Advances in Computer and Electrical Engineering Book Series, 2017, , 294-333.	0.3	2
50	Development of Gas Sensor Model for Detection of NO <sub>2</sub> Molecules Adsorbed on Defect-Free and Defective Graphene. Advances in Computer and Electrical Engineering Book Series, 2017, , 208-223.	0.3	0
51	Influences of Sr-90 beta-ray irradiation on electrical characteristics of carbon nanoparticles. Journal of Applied Physics, 2016, 119, 124510.	2.5	8
52	Graphene embedded surface plasmon resonance based sensor prediction model. Optical and Quantum Electronics, 2016, 48, 1.	3.3	6
53	Modeling and simulation of graphene-oxide-based RRAM. Journal of Computational Electronics, 2016, 15, 602-610.	2.5	13
54	Band structures of graphene nanoscrolls and their dispersion relation near the Fermi point. RSC Advances, 2016, 6, 38753-38760.	3.6	4

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55	Performance prediction of Graphene Nanoscroll and Carbon Nanotube transistors. , 2016, , .		1
56	A charge-based compact modeling of cylindrical surrounding-floating gate MOSFET (S-FGMOSFET) for memory cell application. , 2016, , .		0
57	Carrier velocity effect on carbon nanotube Schottky contact. Semiconductors, 2016, 50, 1056-1059.	0.5	0
58	Explicit continuous charge-based compact model for long channel heavily doped surrounding-gate MOSFETs incorporating interface traps and quantum effects. Semiconductor Science and Technology, 2016, 31, 125020.	2.0	3
59	Strain effect on graphene nanoribbon carrier statistic in the presence of non-parabolic band structure. Chinese Physics B, 2016, 25, 096802.	1.4	2
60	Electrical Property Analytical Prediction on Archimedes Chiral Carbon Nanoscrolls. Journal of Electronic Materials, 2016, 45, 5404-5411.	2.2	10
61	Modelling Effective Charge Density in Graphene-Based DNA Sensor. Science of Advanced Materials, 2016, 8, 1187-1194.	0.7	1
62	Analytical Modeling and Artificial Neural Network (ANN) Simulation of Current-Voltage Characteristics in Graphene Nanoscroll Based Gas Sensors. Plasmonics, 2015, 10, 1713-1722.	3.4	3
63	Conduction Mechanism of Valence Change Resistive Switching Memory: A Survey. Electronics (Switzerland), 2015, 4, 586-613.	3.1	520
64	Modeling of graphene nanoscroll conductance with quantum capacitance effect. Proceedings of SPIE, 2015, , .	0.8	0
65	Performance benchmarking of graphene nanoscroll transistor with 22nm MOSFET model. , 2015, , .		1
66	Sensitivity Modelling of Graphene Nanoscroll-Based NO <sub>2</sub> Gas Sensors. Plasmonics, 2015, 10, 1133-1140.	3.4	12
67	Analytical modeling of the sensing parameters for graphene nanoscroll-based gas sensors. RSC Advances, 2015, 5, 54700-54709.	3.6	6
68	A new approach to model sensitivity of graphene-based gas sensors. Semiconductor Science and Technology, 2015, 30, 045012.	2.0	6
69	Contact Effect on the Currentâ€“Voltage Characteristic of Graphene Nanoribbon Based Schottky Diode. Journal of Computational and Theoretical Nanoscience, 2015, 12, 478-483.	0.4	3
70	Structure and Thickness Optimization of Active Layer in Nanoscale Organic Solar Cells. Plasmonics, 2015, 10, 495-502.	3.4	9
71	Performance Evaluation of Silicon Nanowire Gate-All-Around Field-Effect Transistors and Their Dependence of Channel Length and Diameter. Science of Advanced Materials, 2015, 7, 190-198.	0.7	2
72	A Review of Graphene Based Field Effect Transistor Architecture and Channel Geometry. Science of Advanced Materials, 2015, 7, 2011-2020.	0.7	3

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73	Analytical development and optimization of a grapheneâ€“solution interface capacitance model. Beilstein Journal of Nanotechnology, 2014, 5, 603-609.	2.8	9
74	Graphene nanoribbon field-effect transistor at high bias. Nanoscale Research Letters, 2014, 9, 604.	5.7	11
75	Carrier Statistics and Quantum Capacitance Models of Graphene Nanoscroll. Journal of Nanomaterials, 2014, 2014, 1-6.	2.7	13
76	Modeling of Nanodevices and Nanostructures. Journal of Nanomaterials, 2014, 2014, 1-2.	2.7	1
77	Unified Drain Current Model of Armchair Graphene Nanoribbons with Uniaxial Strain and Quantum Effect. Journal of Nanomaterials, 2014, 2014, 1-7.	2.7	1
78	Impact of strained SiGe on the performance of Vertical Strained SiGe Impact Ionization MOSFET incorporating Dielectric Pocket (VESIMOS-DP). , 2014, , .		0
79	Analytical performance of 3â€“m and 3â€“m + 1 armchair graphene nanoribbons under uniaxial strain. Nanoscale Research Letters, 2014, 9, 598.	5.7	5
80	Quantum confinement effect on trilayer graphene nanoribbon carrier concentration. Journal of Experimental Nanoscience, 2014, 9, 51-63.	2.4	7
81	Analytical model for threshold voltage of double gate bilayer graphene field effect transistors. Microelectronics Reliability, 2014, 54, 44-48.	1.7	8
82	Carrier scattering and impact ionization in bilayer graphene. Journal of Computational Electronics, 2014, 13, 180-185.	2.5	11
83	Analytical modeling of glucose biosensors based on carbon nanotubes. Nanoscale Research Letters, 2014, 9, 33.	5.7	50
84	Analytical prediction of liquid-gated graphene nanoscroll biosensor performance. RSC Advances, 2014, 4, 16153.	3.6	23
85	Analytical study of subthreshold behaviour of double gate bilayer graphene field effect transistors. Semiconductor Science and Technology, 2014, 29, 115011.	2.0	1
86	Modeling the velocity saturation region of graphene nanoribbon transistor. , 2014, , .		0
87	Characterization of vertical strained SiGe impact ionization MOSFET for ultra-sensitive biosensor application. , 2014, , .		0
88	Structural and Properties of Graphene Nanobelts Rolled Up Into Spiral by a Single Graphene Sheet. Journal of Computational and Theoretical Nanoscience, 2014, 11, 601-606.	0.4	7
89	Future of Nanoscale Strained Si/SixGe1â€“x Metal-Oxide Semiconductor Field-Effect Transistor for Performance Metric Evaluation: A Review. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 317-326.	0.5	5
90	A Unified Drainâ€“Current Model of Silicon Nanowire Field-Effect Transistor (SiNWFET) for Performance Metric Evaluation. Science of Advanced Materials, 2014, 6, 354-360.	0.7	7

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91	Carrier Velocity in High-Field Transport of Trilayer Graphene Nanoribbon Field Effect Transistor. Science of Advanced Materials, 2014, 6, 633-639.	0.7	5
92	Simulation of Trigate FET with Semi-Cylindrical Channel to Reduce Corner Effect. , 2013, , .		0
93	Analytical modeling of trilayer graphene nanoribbon Schottky-barrier FET for high-speed switching applications. Nanoscale Research Letters, 2013, 8, 55.	5.7	23
94	Threshold voltage roll-off modelling of bilayer graphene field-effect transistors. Semiconductor Science and Technology, 2013, 28, 125020.	2.0	3
95	Performance Analysis of Vertical Strained-SiGe Impact Ionization MOSFET Incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
96	Single and dual strained channel analysis of vertical strained &#x2014; SiGe impact ionization MOSFET (VESIMOS). , 2013, , .		5
97	QUANTUM CAPACITANCE EFFECT ON ZIG-ZAG GRAPHENE NANOSCROLLS (ZGNS) (16, 0). Modern Physics Letters B, 2013, 27, 1350002.	1.9	4
98	The effect of uniaxial strain on graphene nanoribbon carrier statistic. Nanoscale Research Letters, 2013, 8, 479.	5.7	3
99	Schottky barrier lowering effect on graphene nanoribbon based schottky diode. , 2013, , .		1
100	Mobility enhancement on Vertical Strained-SiGe Impact Ionization MOSFET incorporating Dielectric Pocket (VESIMOS-DP). , 2013, , .		0
101	Performance analysis of single and dual channel vertical strained SiGe impact ionization MOSFET (VESIMOS). , 2013, , .		0
102	Threshold Voltage Variation of Nanoscale Strained Si/Si<SUB>1â€™</SUB>Ge<SUB>x</SUB> MOSFETs in the Presence of Punch Through Effect. Journal of Computational and Theoretical Nanoscience, 2013, 10, 2366-2370.	0.4	0
103	Mitigating Breakdown Voltage with Dual Channel Vertical Strained SiGe Impact Ionization MOSFET (VESIMOS). , 2013, , .		0
104	Quantum Mechanical Effects on the Threshold Voltage of Nanoscale Dual Channel Strained Si/Strained Si/Si<SUB>1â€™</SUB>Ge<SUB>x</SUB> MOSFETs in the Presence of Punch Through Effect. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1231-1235.	0.4	1
105	Bilayer Graphene Nanoribbon Mobility Model in Ballistic Transport Limit. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1262-1265.	0.4	1
106	Perpendicular Electric Field Effect on Bilayer Graphene Carrier Statistic. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1975-1978.	0.4	8
107	Graphene Nanoribbon Field Effect Transistor Logic Gates Performance Projection. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1164-1170.	0.4	15
108	The Effect of Interconnect on the Circuit Performance of 22 nm Graphene Nanoribbon Field Effect Transistor and MOSFET. Journal of Computational and Theoretical Nanoscience, 2013, 10, 1305-1309.	0.4	2

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109	Geometry Effect on Graphene Nanoscrolls Band Cap. Journal of Computational and Theoretical Nanoscience, 2013, 10, 581-586.	0.4	2
110	The Effect of Bilayer Graphene Nanoribbon Geometry on Schottky-Barrier Diode Performance. Journal of Nanomaterials, 2013, 2013, 1-8.	2.7	2
111	An Analytic Model for Estimating the Length of the Velocity Saturated Region in Double Gate Bilayer Graphene Transistors. Journal of Nanomaterials, 2013, 2013, 1-5.	2.7	1
112	The impact of germanium in strained Si/relaxed Si <sub>1-x</sub> Ge <sub>x</sub> on carrier performance in non-degenerate and degenerate regimes. Journal of Semiconductors, 2013, 34, 062001.	3.7	1
113	The effect of width on graphene nanoribbon density of state under uniaxial strain. , 2013, , .		1
114	Body doping analysis of vertical strained-SiGe Impact Ionization MOSFET incorporating dielectric pocket (VESIMOS-DP). , 2013, , .		0
115	ENERGY QUANTIZATION ON THE CURRENT-VOLTAGE CHARACTERISTIC OF NANOSCALE TWO-DIMENSIONAL MOSFET. International Journal of Modern Physics B, 2013, 27, 1350077.	2.0	1
116	The Effect of Effective Channel Length on a Silicon Nanowire Fin Field Effect Transistor. Journal of Computational and Theoretical Nanoscience, 2013, 10, 964-967.	0.4	0
117	Current-Voltage Characteristics of Bilayer Graphene Nanoribbon Field Effect Transistor. Journal of Computational and Theoretical Nanoscience, 2013, 10, 738-741.	0.4	2
118	Performance of Bilayer Graphene Nanoribbon Schottky Diode in Comparison with Conventional Diodes. Journal of Computational and Theoretical Nanoscience, 2013, 10, 323-327.	0.4	10
119	The Potential Barrier of Graphene Nanoribbon Based Schottky Diode. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 281-284.	0.5	1
120	Analytical Modeling of Monolayer Graphene-based NO <sub>2</sub> Sensor. Sensor Letters, 2013, 11, 270-275.	0.4	16
121	Low-Dimensional Silicon Nanowire (SiNW) Conductance Model. Quantum Matter, 2013, 2, 417-420.	0.2	0
122	Schottky Current in Carbon Nanotube-Metal Contact. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1554-1557.	0.4	6
123	Effect of Graphene Nanoribbons Layers on Its Band Energy and the Electrical Properties. Journal of Computational and Theoretical Nanoscience, 2012, 9, 2082-2085.	0.4	1
124	Two Dimensional Analytical Threshold Voltage Model of Nanoscale Strained Si <sub>1-x</sub> Ge <sub>x</sub> MOSFETs Including Quantum Mechanical Effects. Journal of Computational and Theoretical Nanoscience, 2012, 9, 441-447.	0.4	1
125	The Effect of Applied Voltage on the Carrier Effective Mass in ABA Trilayer Graphene Nanoribbon. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1618-1621.	0.4	10
126	Improved dead time response for Si Avalanche Photodiode. , 2012, , .		0



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127	Simulation of nanoscale dual-channel strained Si/Strained Si <sub>1-x</sub> Ge <sub>x</sub> /Relaxed Si <sub>1-x</sub> Ge <sub>x</sub> PMOSFET. , 2012, , .		0
128	Temperature effect on quantum capacitance zig-zag graphene nanoscrolls (ZGNS) (16,0). , 2012, , .		0
129	Modeling of Drain Current for Grooved-Gate MOSFET. Journal of Computational and Theoretical Nanoscience, 2012, 9, 1596-1602.	0.4	0
130	Investigation of incorporating dielectric pocket (DP) on Vertical Strained-SiGe Impact Ionization MOSFET (VESIMOS-DP). , 2012, , .		7
131	Enhanced performance analysis of vertical strained-sigeimpact Ionization MOSFET (VESIMOS). , 2012, , .		9
132	Focused ion beam milling of exfoliated graphene for prototyping of electronic devices. Microelectronic Engineering, 2012, 98, 313-316.	2.4	17
133	CHANNEL CONDUCTANCE OF ABA STACKING TRILAYER GRAPHENE NANORIBBON FIELD-EFFECT TRANSISTOR. Modern Physics Letters B, 2012, 26, 1250047.	1.9	10
134	Band energy effect on carrier velocity limit in graphene nanoribbon. Journal of Experimental Nanoscience, 2012, 7, 62-73.	2.4	5
135	Simulation and Fabrication of Extended Gate Ion Sensitive Field Effect Transistor for Biosensor Application. Communications in Computer and Information Science, 2012, , 396-403.	0.5	6
136	Monolayer Graphene Nanoribbon p-n Junction. Journal of Nanoengineering and Nanomanufacturing, 2012, 2, 375-378.	0.3	6
137	Monolayer Graphene Nanoribbon Homo Junction Characteristics. Science of Advanced Materials, 2012, 4, 753-756.	0.7	9
138	The Sub-Band Effect on the Graphene Nanoribbon Based Field-Effect Transistor. Journal of Nanoelectronics and Optoelectronics, 2012, 7, 361-365.	0.5	0
139	Biased voltage boundary condition to operate Bilayer Graphene in the insulating region. , 2011, , .		0
140	EFFECTIVE MOBILITY MODEL OF GRAPHENE NANORIBBON IN PARABOLIC BAND ENERGY. Modern Physics Letters B, 2011, 25, 739-745.	1.9	8
141	A review on carbon-based materials as on-chip interconnects. Proceedings of SPIE, 2011, , .	0.8	2
142	Current-voltage modeling of Bilayer Graphene Nanoribbon Schottky Diode. , 2011, , .		2
143	Bilayer Graphene Nanoribbon Carrier Statistic in Degenerate and Non Degenerate Limit. Journal of Computational and Theoretical Nanoscience, 2011, 8, 2029-2032.	0.4	7
144	An Analytical Threshold Voltage Model for the Vertical Sidewall Mosfet with a Curved-Channel. Journal of Computational and Theoretical Nanoscience, 2011, 8, 2299-2306.	0.4	0

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145	CARBON NANOTUBE CAPACITANCE MODEL IN DEGENERATE AND NONDEGENERATE REGIMES. , 2011, , .		4
146	DRIFT VELOCITY AND MOBILITY OF A GRAPHENE NANORIBBON IN A HIGH MAGNITUDE ELECTRIC FIELD. , 2011, , .		4
147	BILAYER GRAPHENE NANORIBBON CARRIER STATISTICS IN THE DEGENERATE REGIME. , 2011, , .		4
148	Single Wall Carbon Nanotube Field Effect Transistor Model. Journal of Computational and Theoretical Nanoscience, 2011, 8, 261-267.	0.4	1
149	Performance and Microstructural Study on Soap Using Different Fatty Acids and Cations. Journal of Surfactants and Detergents, 2011, 14, 463-471.	2.1	5
150	Influence of Body-Tied and Floating-Body Structure in Double Gate Vertical n-MOSFET. , 2011, , .		0
151	Modeling of Quantum Capacitance in Graphene Nanoribbon. AIP Conference Proceedings, 2011, , .	0.4	6
152	Monolayer graphene nanoribbon p-n junction. , 2011, , .		2
153	Ballistic Conductance Model of Bilayer Graphene Nanoribbon (BGN). Journal of Computational and Theoretical Nanoscience, 2011, 8, 1993-1998.	0.4	12
154	LOW-FIELD MOBILITY MODEL ON PARABOLIC BAND ENERGY OF GRAPHENE NANORIBBON. Modern Physics Letters B, 2011, 25, 281-290.	1.9	4
155	Bilayer Graphene Nanoribbon Conductance Model in Parabolic Band Structure. , 2011, , .		0
156	Analytical modeling of high performance single-walled carbon nanotube field-effect-transistor. Microelectronics Journal, 2010, 41, 579-584.	2.0	16
157	Investigation of pillar thickness variation effect on oblique rotating implantation (ORI)-based vertical double gate MOSFET. Microelectronics Journal, 2010, 41, 827-833.	2.0	2
158	Graphene Nanoribbon Conductance Model in Parabolic Band Structure. Journal of Nanomaterials, 2010, 2010, 1-4.	2.7	50
159	Modelling of Graphene Nanoribbon Fermi Energy. Journal of Nanomaterials, 2010, 2010, 1-6.	2.7	20
160	Numerical Simulation Analysis of CMOS Compatible Process of 50 nm Vertical Single and Double Gate NMOSFET. , 2010, , .		0
161	Numerical Simulation Characterization of 50nm MOSFET Incorporating Dielectric Pocket (DP-MOSFET). , 2010, , .		1
162	CARBON NANOTUBE BAND STRUCTURE EFFECT ON CARBON NANOTUBE FIELD EFFECT TRANSISTOR. , 2010, , .		1

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163	The Corner Effects of a Curved-Channel MOSFET. , 2010, , .		0
164	Bilayer Graphene nanoribbon conductance model in parabolic band structure. , 2010, , .		0
165	Carbon nanotube conductance model in parabolic band structure. , 2010, , .		10
166	Nonparabolic band structure effect on carrier transport in semiconducting graphene nanoribbons. , 2010, , .		0
167	Graphene Nanoribbon Fermi Energy Model in Parabolic Band Structure. , 2010, , .		2
168	Modeling of quantum capacitance of Graphene Nanoribbons. , 2010, , .		7
169	Investigation of short channel immunity of fully depleted double gate MOS with vertical structure. , 2010, , .		0
170	Enhanced performance of vertical double gate MOSFET (VDGM) with oblique rotating implantation (ORI) method. , 2010, , .		1
171	Reduced parasitic capacitances analysis of nanoscale vertical MOSFET. , 2010, , .		1
172	The influence of body-tied and floating-body structure in Double Gate Vertical n-MOSFET. , 2010, , .		0
173	The Future of Non-planar Nanoelectronics MOSFET Devices: A Review. Journal of Applied Sciences, 2010, 10, 2136-2146.	0.3	17
174	Analytical Study of Carrier Statistic in 2-Dimensional Nanoscale P-MOS. , 2009, , .		1
175	Analytical Study Of Drift Velocity In P-Type Silicon Nanowires. , 2009, , .		0
176	The high-field drift velocity in degenerately-doped silicon nanowires. International Journal of Nanotechnology, 2009, 6, 601.	0.2	22
177	Scattering-limited and ballistic transport in a nano-CMOS circuit. Microelectronics Journal, 2009, 40, 581-583.	2.0	9
178	Ballistic mobility and saturation velocity in low-dimensional nanostructures. Microelectronics Journal, 2009, 40, 540-542.	2.0	26
179	Currentâ€“voltage characteristics of a silicon nanowire transistor. Microelectronics Journal, 2009, 40, 547-549.	2.0	23
180	Analytical study of drift velocity in N-type silicon nanowires. , 2009, , .		1

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181	Design and simulation analysis of nanoscale vertical MOSFET technology. , 2009, , .		1
182	The drain velocity overshoot in an 80 nm metal-oxide-semiconductor field-effect transistor. Journal of Applied Physics, 2009, 105, 074503.	2.5	31
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